



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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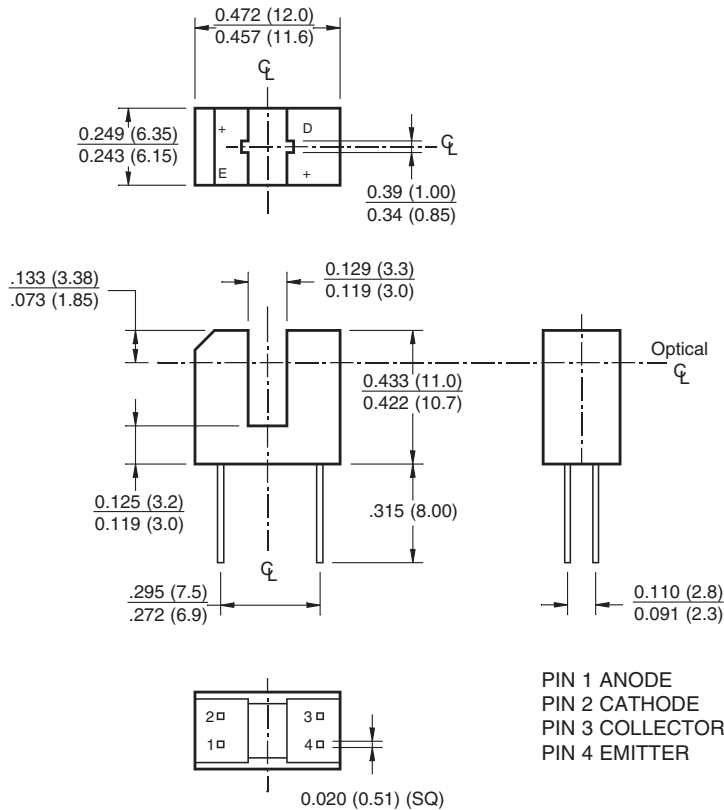


H22B1

H22B2

H22B3

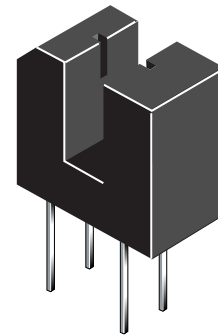
PACKAGE DIMENSIONS



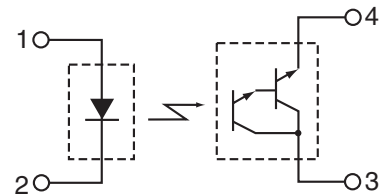
PIN 1 ANODE
PIN 2 CATHODE
PIN 3 COLLECTOR
PIN 4 EMITTER

NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The H22B1, H22B2 and H22B3 consist of a gallium arsenide infrared emitting diode coupled with a silicon photodarlington in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.

FEATURES

- Opaque housing
- Low cost
- .035" apertures
- High $I_{C(ON)}$

H22B1

H22B2

H22B3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	T_{OPR}	-55 to +100	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to +100	$^\circ\text{C}$
Soldering Temperature (Iron) ^(2,3 and 4)	T_{SOL-I}	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) ^(2 and 3)	T_{SOL-F}	260 for 10 sec	$^\circ\text{C}$
INPUT (EMITTER)			
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	6	V
Power Dissipation ⁽¹⁾	P_D	100	mW
OUTPUT (SENSOR)			
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Collector Voltage	V_{ECO}	6	V
Collector Current	I_C	40	mA
Power Dissipation ($T_C = 25^\circ\text{C}$) ⁽¹⁾	P_D	150	mW

NOTES:

1. Derate power dissipation linearly 1.67 mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6 mm) minimum from housing.

H22B1

H22B2

H22B3

ELECTRICAL/OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	TEST CONDITIONS	SYMBOL	DEVICES	MIN	TYP	MAX	UNITS
INPUT (EMITTER)							
Forward Voltage	$I_F = 60 \text{ mA}$	V_F	All	—	—	1.7	V
Reverse Breakdown Voltage	$I_R = 10 \mu\text{A}$	V_R	All	6.0	—	—	V
Reverse Leakage Current	$V_R = 3 \text{ V}$	I_R	All	—	—	1.0	μA
OUTPUT (SENSOR)							
Emitter to Collector Breakdown	$I_F = 100 \mu\text{A}, E_e = 0$	BV_{ECO}	All	7.0	—	—	V
Collector to Emitter Breakdown	$I_C = 1 \text{ mA}, E_e = 0$	BV_{CEO}	All	30	—	—	V
Collector to Emitter Leakage	$V_{CE} = 25 \text{ V}, E_e = 0$	I_{CEO}	All	—	—	100	nA
COUPLED							
On-State Collector Current	$I_F = 2 \text{ mA}, V_{CE} = 1.5 \text{ V}$	$I_{C(ON)}$	H22B1	0.5	—	—	mA
			H22B2	1.0	—	—	
			H22B3	2.0	—	—	
	$I_F = 5 \text{ mA}, V_{CE} = 1.5 \text{ V}$		H22B1	2.5	—	—	
			H22B2	5.0	—	—	
			H22B3	10	—	—	
	$I_F = 10 \text{ mA}, V_{CE} = 1.5 \text{ V}$		H22B1	7.5	—	—	
			H22B2	14	—	—	
			H22B3	25	—	—	
Saturation Voltage	$I_F = 10 \text{ mA}, I_C = 1.8 \text{ mA}$	$V_{CE(SAT)}$	All	—	—	1.0	V
	$I_F = 60 \text{ mA}, I_C = 50 \text{ mA}$		H22B1/2	—	—	1.5	V
Turn-On Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$	t_{on}	All	—	45	—	μs
	$I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75\Omega$		All	—	7	—	
Turn-Off Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$	t_{off}	All	—	250	—	μs
	$I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75\Omega$		All	—	45	—	

H22B1

H22B2

H22B3

Figure 1. Output Current vs. Input Current

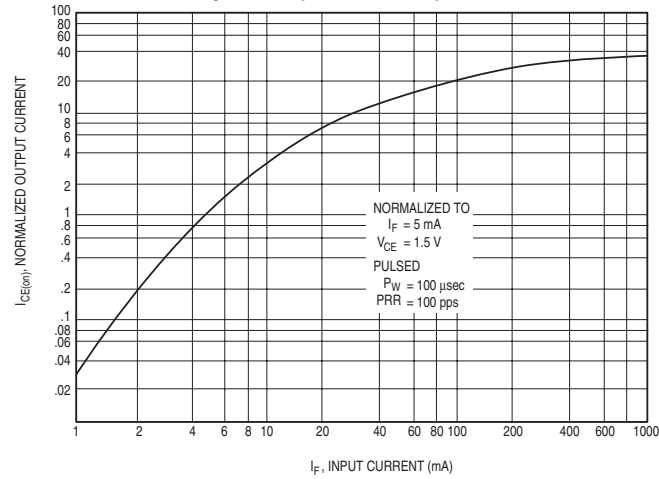


Figure 2. Output Current vs. Temperature

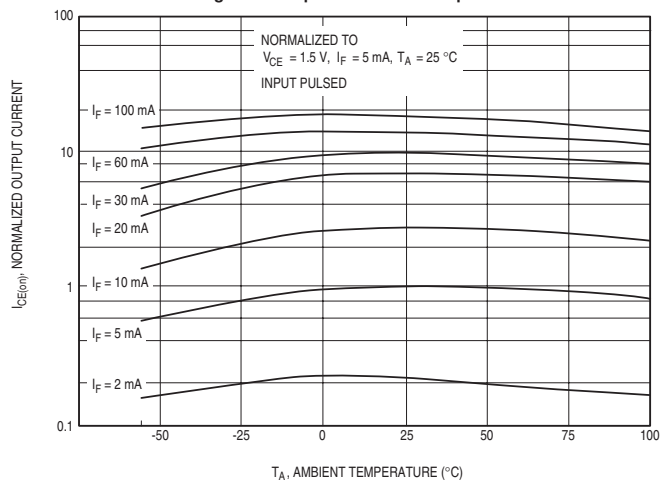
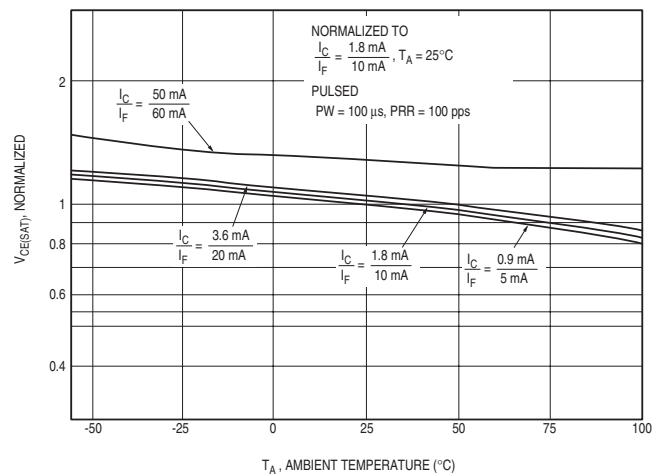


Figure 3. $V_{CE(SAT)}$ vs. Temperature



H22B1

H22B2

H22B3

Figure 4. Leakage Current vs. Temperature

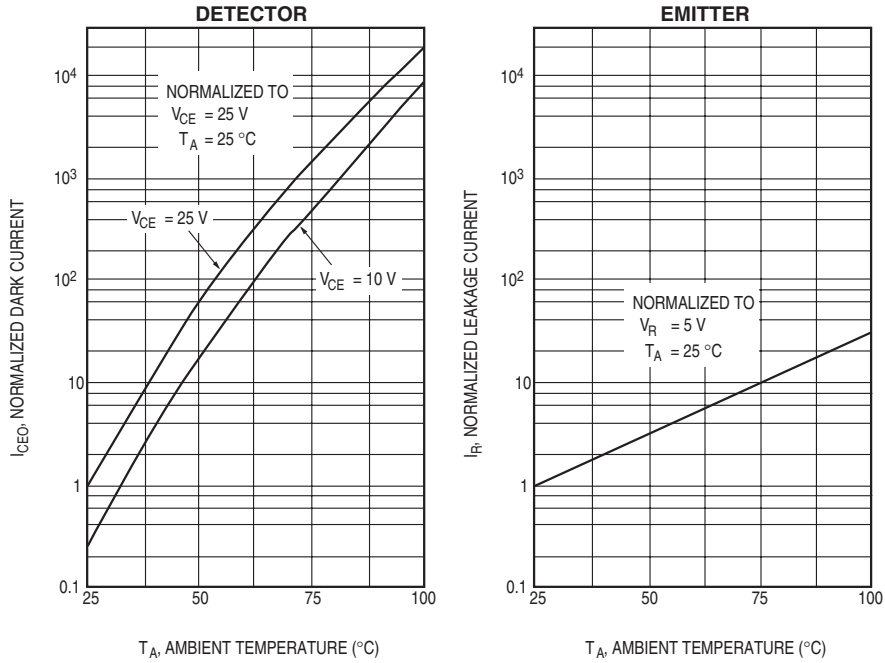


Figure 5. Switching Speed vs. R_L

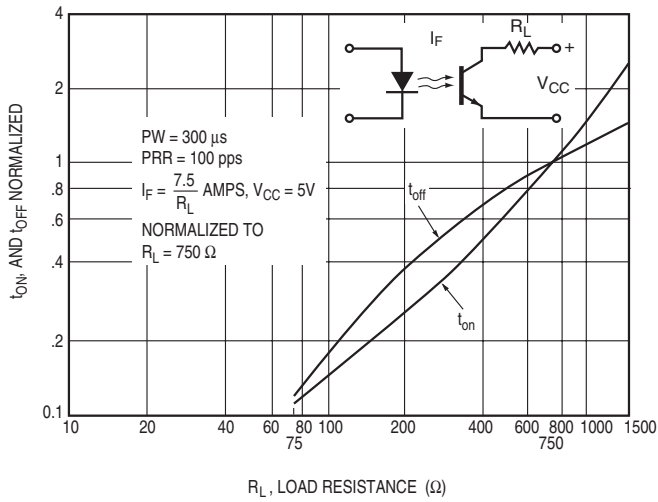
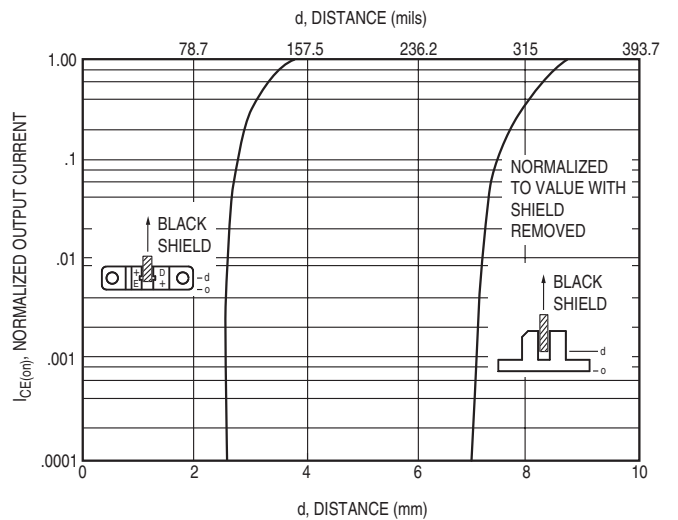


Figure 6. Output Current vs. Distance



H22B1

H22B2

H22B3

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